

HIGH EFFICIENCY ULTRAFAST DIODE
MAIN PRODUCT CHARACTERISTICS

I_{F(AV)}	1 A
V_{RRM}	200 V
T_j (max)	175 °C
V_F (max)	0.78 V
t_{rr} (max)	20 ns

FEATURES AND BENEFITS

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery times
- High junction temperature

DESCRIPTION

The STTH102, which is using ST's new 200V planar technology, is specially suited for switching mode base drive & transistor circuits.

The device is also intended for use as a free wheeling diode in power supplies and other power switching applications.


ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak reverse voltage		200	V
I _{F(AV)}	Average forward current	T _I = 130°C δ = 0.5	1	A
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms Sinusoidal	50	A
T _{stg}	Storage temperature range		- 65 + 175	°C
T _j	Maximum operating junction temperature		+ 175	°C

THERMAL PARAMETERS

Symbol	Parameter	Maximum	Unit
R _{th(j-a)}	Junction to ambient*	50	°C/W

* On infinite heatsink with 10mm length.

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			1	μA
		$T_j = 125^\circ\text{C}$			1	25	
V_F^{**}	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 1\text{A}$			0.97	V
		$T_j = 125^\circ\text{C}$			0.68	0.78	

Pulse test: * $t_p = 5\text{ms}$, $\delta < 2\%$

** $t_p = 380\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.130 \times I_{F(RMS)}^2$$

DYNAMIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 0.5\text{A}$ $I_{rr} = 0.25\text{A}$ $I_R = 1\text{A}$	$T_j = 25^\circ\text{C}$		12	20	ns
t_{fr}	Forward recovery time	$I_F = 1\text{A}$ $dI_F/dt = 50\text{A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$	$T_j = 25^\circ\text{C}$		50		ns
V_{FP}	Forward recovery voltage		$T_j = 25^\circ\text{C}$		1.8		V

Fig. 1: Average forward power dissipation versus average forward current.

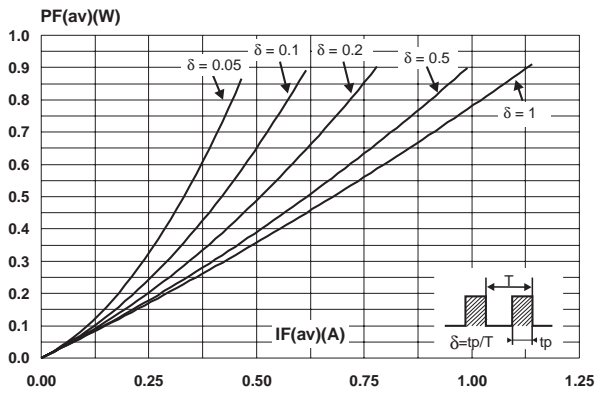


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$).

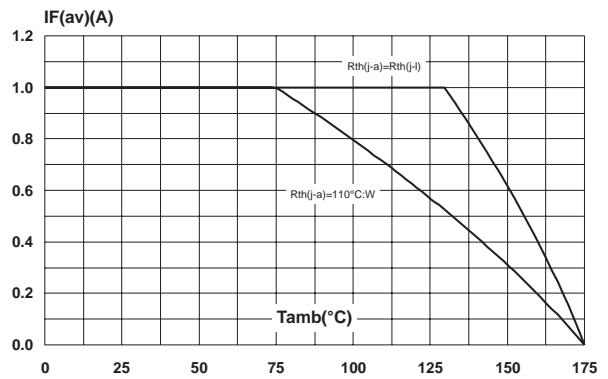


Fig. 3: Thermal resistance versus lead length.

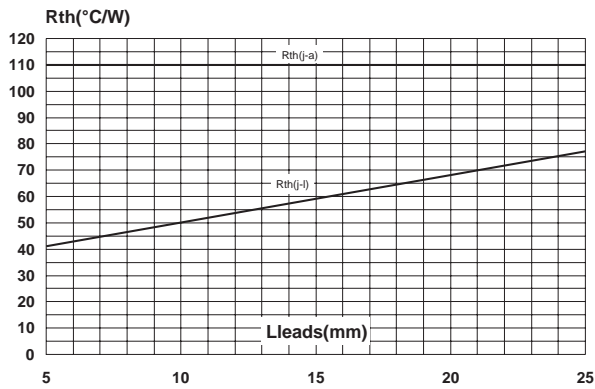


Fig. 4: Relative variation of thermal impedance junction ambient versus pulse duration (Printed circuit board epoxy FR4, Leads = 10mm).

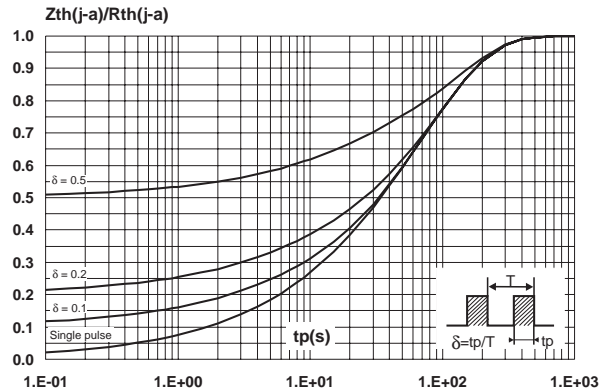


Fig. 5: Forward voltage drop versus forward current.

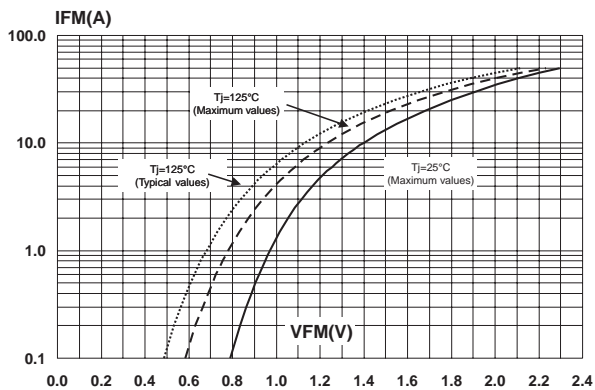


Fig. 6: Junction capacitance versus reverse voltage applied (typical values).

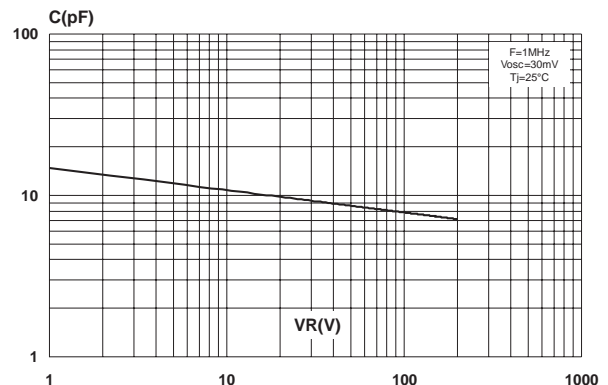


Fig. 7: Reverse recovery time versus dI/dt (90% confidence).

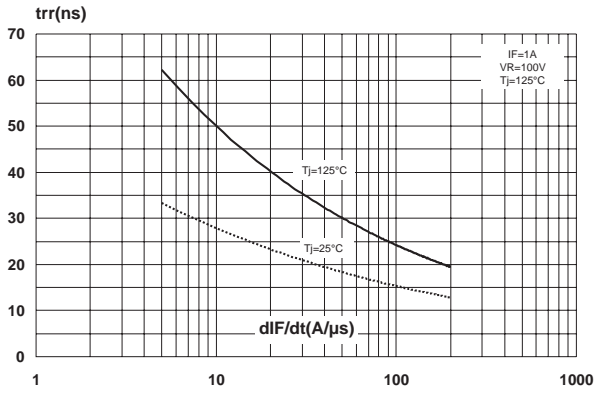


Fig. 8: Peak reverse recovery current versus dI/dt (90% confidence).

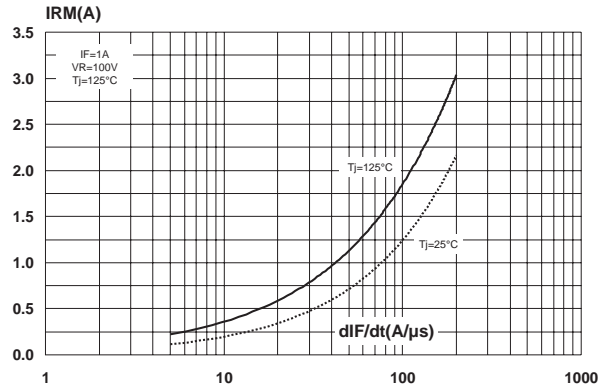
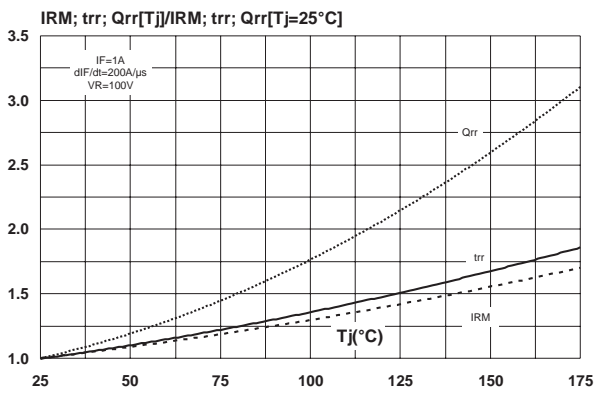


Fig. 9: Relative variations of dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA
DO-41

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.1	5.20	0.160	0.205
B	2	2.71	0.080	0.107
C	25.4		1	
D	0.712	0.863	0.028	0.034

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH102	STTH102	DO-41	0.34 g	2000	Ammopack
STTH102RL	STTH102	DO-41	0.34 g	5000	Tape & reel

- Cooling method: by conduction (method A)
- Epoxy meets UL 94,V0

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